

**REMARKS**

The Office Action mailed July 1, 2005, was received and its contents carefully reviewed. Claims 1-26 were previously presented. In response to the July 1, 2005, Office Action, Applicants canceled claims 1-7, 12, 13, 15, and 16. Additionally, Applicants amended 8, 9, 11, 18, and 19 to provide additional context and details regarding the present invention. Support for these amendments may be found throughout the specification and at least on pages 16, line 5 to page 18, line 28; and on page 28, lines 3-5. As such, Applicants respectfully submit that no new matter was introduced by these amendments.

As now recited, claims 8-11, 14, and 17-26 are currently pending and are believed to be in condition for allowance. With respect, Applicants submit that the present Amendment complies with the submission requirements of a Request for Continued Examination and request reconsideration of the present application in light of the above amendments and the following remarks.

**A. Allowable Subject Matter**

Applicants acknowledge and thank the Examiner for indicating that claims 21-26 are allowed.

**B. 35 U.S.C. § 112, first paragraph**

Claims 1-20 stand rejected under 35 U.S.C. § 112, first paragraph, as failing to comply with the written description requirement. The Examiner asserts that these claims contain subject matter that was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventors, at the time the application was filed, had possession of the claimed invention.

Applicants canceled claims 1-7 by the above amendment and therefore do not address their rejection. However, with regard to independent claim 8, the Examiner asserts that the claim 8 limitation "a wiring connected to the gate electrodes of TFT in

the peripheral circuit region and formed over the first insulating film" is not supported in the originally filed disclosure. Applicants respectfully request reconsideration of this rejection in light of the above amendments and the following remarks.

Amended independent claim 8 now recites, "A semiconductor device comprising a pixel region; a peripheral circuit region placed in at least one part of an area surrounding the pixel region; gate electrodes of TFTs formed in the peripheral circuit region; a first insulating film formed over the gate electrodes; a short distance wiring connected to the gate electrodes and formed over the first insulating film; a second insulating film formed over the short distance wiring; and a long distance wiring formed over the second insulating film, wherein the gate electrodes in different TFTs are isolated from one another."

As alluded in Applicants' previous response, the amended term "short distance" and "long distance" are not merely labels, but are relative terms of significance. To wit, the present invention provides a technique for reducing the area of a peripheral circuit region with respect to a pixel region and improves the aperture ratio of the pixel region by giving the peripheral circuit region (border frame) a smaller width through a multilayer wiring.

With regard to amended claim 8, a gate electrode may be given the function of a gate electrode and formed not to have the function of a wiring by isolating a gate electrode in one TFT from a gate electrode in another TFT. However, a gate electrode may also be formed to function as a short distance wiring by forming a wiring in an upper or lower layer of a gate electrode and electrically connecting the gate electrode. This gives the wiring the wiring function of the gate electrode as well as the function of a short distance wiring. This makes it possible to use a material that is not resistant to thermal activation for the wiring in the layer above the gate electrode. Therefore, the range of selection of wiring material is widened. For further details regarding this configuration, please see page 13, line 12 to page 14, line 7 of the specification.

Additionally, the drain electrode 35 and the first and second wirings 39, 43 as a whole can be a multilayer wiring having a function of a short distance wiring with a short length (see page 28, lines 3-5). That is, drain electrode 35, the first and second wirings 39 and 43 in FIG. 5B may be regarded as a short distance wiring described in Embodiment Mode 3. Additionally, "a wiring is formed in an upper or lower layer of a gate electrode and is electrically connected to the gate electrode to give the wiring the wiring function of the gate electrode in prior art as well as the function of a short distance wiring, one of the wirings of prior art that has a short wiring length," on page 16, lines 9-12 of the specification, provides additional details. The short distance wiring described in Embodiment Mode 3 is formed in an upper layer of gate electrodes 28, 29 and is electrically connected to the gate electrodes 28, 29. Accordingly, the specification disclosed gate electrodes 28, 29 of TFTs in the peripheral circuit region, the insulating film 31 formed over the gate electrodes 28, 29, and the short distance wiring connected to the gate electrodes 28, 29 and formed over the insulating film 31.

In the light of the above amendment, the disclosure of the short distance wiring in the original disclosure, and the above remarks, Applicants respectfully assert that amended claim 8 contains subject matter that was described in the specification in such a way as to reasonably convey the invention to one skilled in the relevant art as illustrated at least on page 16, line 5 to page 18, line 24 and further on page 28, lines 3-5 of the original specification.

Applicants canceled claims 1-7, 12, 13, 15, and 16 by the above Amendment and therefore does not address their previous rejection. However, dependent claims 9-11, 14, and 17-20 are dependent upon amended claim 8, and thereby include all the limitations of independent claim 8, while reciting additional features of the present invention. As such, Applicants respectfully request reconsideration and withdrawal of the rejection of claims 8-11, 14, 17-20 under 35 U.S.C. § 112, first paragraph.

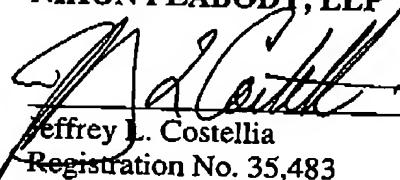
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**C. Conclusion**

In view of the above amendments and remarks, Applicants respectfully request the Examiner's reconsideration of this application and the timely allowance of the pending claims.

Respectfully submitted,

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